

2SB1322A

Silicon PNP epitaxial planer type

For low-frequency power amplification
Complementary to 2SD1994A

Features

- Allowing supply with the radial taping.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1.5	A
Collector current	I_C	-1	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

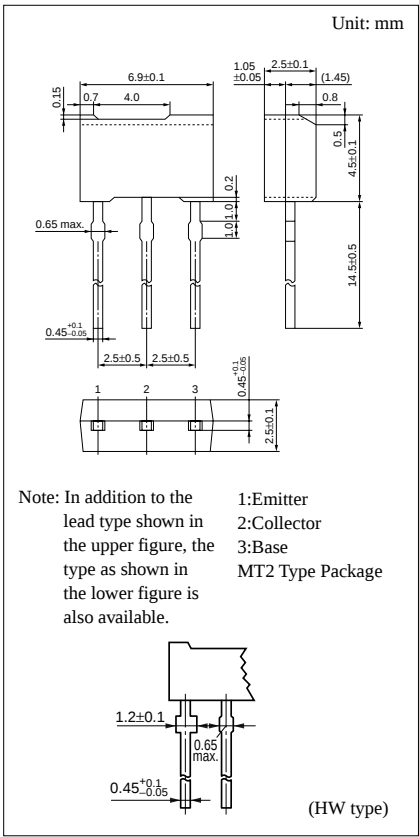
Electrical Characteristics (Ta=25°C)

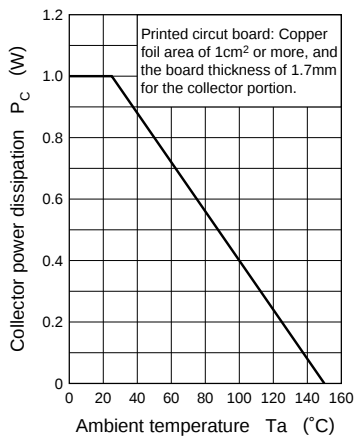
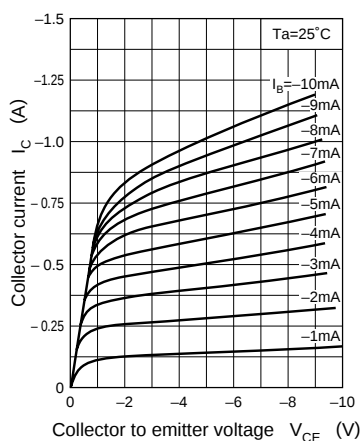
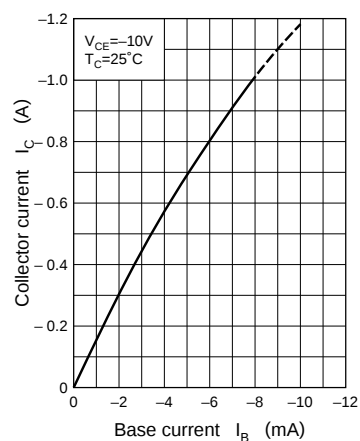
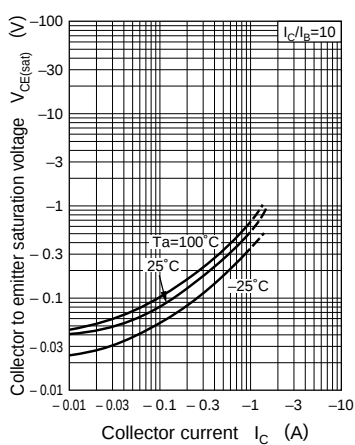
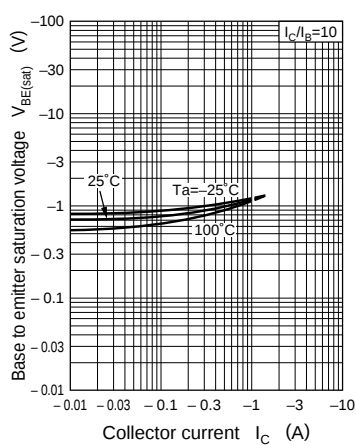
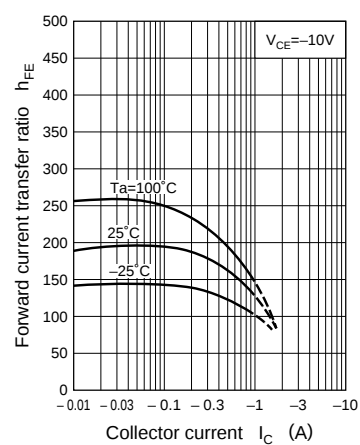
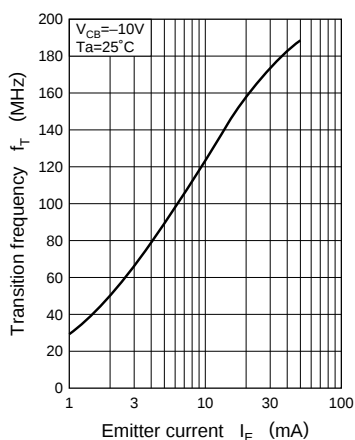
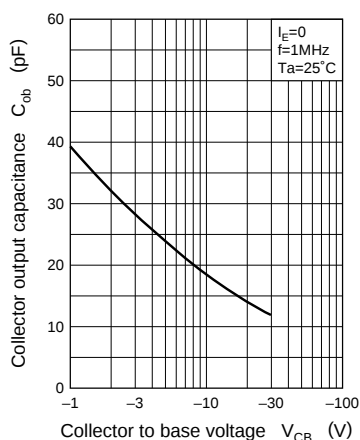
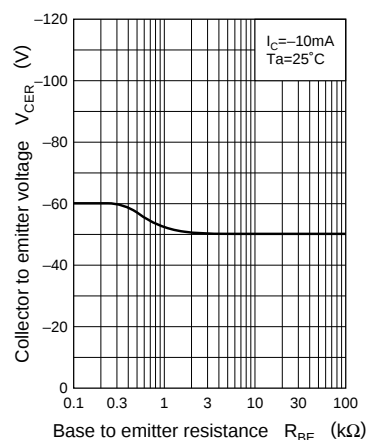
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			- 0.1	μA
Collector to base voltage	V_{CBO}	$I_C = -10μA, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10μA, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = -10V, I_C = -500mA^{*2}$	85		340	
	h_{FE2}	$V_{CE} = -5V, I_C = -1mA^{*2}$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA^{*2}$			- 0.4	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA^{*2}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	30	pF

^{*2} Pulse measurement

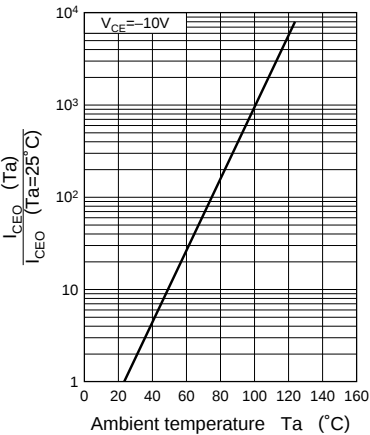
^{*1} h_{FE1} Rank classification

Rank	Q	R	S
h_{FE1}	85 ~ 170	120 ~ 240	170 ~ 340



$P_C - T_a$  $I_C - V_{CE}$  $I_C - I_B$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$  $V_{CER} - R_{BE}$ 

$I_{CEO} - T_a$



Area of safe operation (ASO)

